Unit: mm

TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

# MT6C04AS

VHF-UHF Band Low Noise Amplifier Application VHF-UHF Band Oscillator Application

 Two devices are built into the sES6 package, which is smaller and thinner than the super-thin and ultra-super mini (6-pin) ES6 package.

#### **Mounted Devices**

	Q1/Q2: SSM (TESM)
Three pin (SSM/TESM) type part No.	MT3S04AS (MT3S04AT)

## Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Q1/Q2	Unit	
Collector-base voltage	$V_{CBO}$	10	V	
Collector-emitter voltage	$V_{CEO}$	5	V	
Emitter-base voltage	$V_{EBO}$	2	V	
Collector current	I <sub>C</sub>	40	mA	
Base current	ΙΒ	10	mA	
Collector power dissipation	P <sub>C</sub> (Note 1)	100	mW	
Junction temperature	Tj	125	°C	
Storage temperature range	T <sub>stg</sub>	<b>−55~125</b>	°C	

1. COLLECTOR1 4. EMITTER2
2. EMITTER1 5. BASE2
3. COLLECTOR2 6. BASE1

JEDEC —

JEITA —

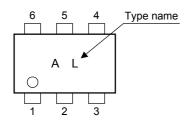
2-2Q1B

Weight: g (typ.)

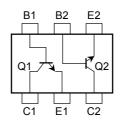
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Note 1: Total power dissipation of Q1 and Q2 mounted on the circuit board

## Marking



## **Pin Assignment**



## Electrical Characteristics Q1/Q2-Side (Ta = 25°C)

Characteristics	Symbol	Test Condition		Тур.	Max	Unit	
Collector cut-off current	I <sub>CBO</sub>	$V_{CB} = 5 \text{ V}, I_{E} = 0$		_	0.1	μΑ	
Emitter cut-off current	I <sub>EBO</sub>	$V_{EB} = 1 \text{ V, } I_{C} = 0$		_	1	μΑ	
DC current gain	h <sub>FE</sub>	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}$		_	160	_	
Transition frequency	f <sub>T</sub> (1)	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}$	2	4.5	_	GHz	
	f <sub>T</sub> (2)	$V_{CE} = 3 \text{ V}, I_{C} = 7 \text{ mA}$	5	7	_	GHz	
Insertion gain	S <sub>21e</sub>   <sup>2</sup> (1)	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}, f = 1 \text{ GHz}$	_	8.5	_	dB	
	S <sub>21e</sub>   <sup>2</sup> (2)	$V_{CE} = 3 \text{ V}, I_{C} = 20 \text{ mA}, f = 1 \text{ GHz}$	7.5	11	_		
Noise figure	NF (1)	$V_{CE} = 1 \text{ V, } I_{C} = 5 \text{ mA, } f = 1 \text{ GHz}$	_	1.3	2.2	dB	
	NF (2)	$V_{CE} = 3 \text{ V}, I_{C} = 7 \text{ mA}, f = 1 \text{ GHz}$		1.2	2	ub	
Reverse transfer capacitance	C <sub>re</sub>	$V_{CB} = 1 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$ (Note	2) —	0.9	1.25	pF	

Note 2:  $C_{re}$  is measured by 3 terminal method with capacitance bridge.

#### **Caution**

This device is sensitive to electrostatic discharge. Please make enough tool and equipment earthed when you handle.

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